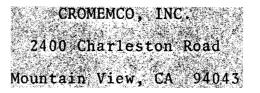
CROMEMCO 16KZ RAM CARD TECHNICAL MANUAL



# CROMEMCO 16KZ RAM CARD TECHNICAL MANUAL

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#### 1.0 INTRODUCTION

The Cromemco 16KZ is a high-speed 16K RAM card designed for the S-100 microcomputer bus. The 16KZ can operate at 2 MHz or 4 MHz system clock rates with no wait states whatsoever. A special Bank Select feature is incorporated on the 16KZ that allows memory space to be organized into as many as 8 banks of 64K each. The memory banks in which the 16KZ resides are selected by switches on each 16KZ card; the active banks of memory are selected under software control. The 16KZ also contains Direct Memory Access Override Circuitry that allows any DMA device to access different banks of memory during DMA operations than otherwise.

With its high-speed capability and memory bank expandability, the Cromemco 16KZ is designed to be a card of lasting value. It is particularly well-suited for use with the Cromemco line of S-100 bus computer equipment. It is also compatible with other S-100 bus computers including the Altair 8800 and the Imsai 8080.

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#### 2.0 INITIAL SWITCH AND JUMPER SETUP

#### 2.1 Logical Address Block Select

The 16KZ RAM board may be located in any one of four 16K blocks of memory space. The Block Select switches, labeled A14 and A15, are part of a 4-place DIP switch located in the upper middle of the card. These switches control address bits A14 and A15 respectively. Setting a switch to the UP position enables the card to respond to a high logic level in that address bit. Table I below summarizes the switch settings for each block.

Table I

Origin Address	End Address	<u>A15</u>	<u>A14</u>
0	3FFF	0	0
4000	7FFF	0	1
8000	BFFF	1	0
C000	FFFF	1	1

#### 2.2 Memory Bank Mapping Select

With the unique, software-controllable Cromemco Memory Bank Select feature, the 16KZ card may be mapped to any combination of 8 levels of 64K memory space. The 8-place DIP switch in the upper middle of the card controls bank selection. A switch in the UP position assigns the card to the specific memory bank.

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On power-up the active memory bank is Bank 0. Only memory boards mapped to this bank are immediately active after power-up. At this point, any bank or banks may be enabled under software control, by addressing I/O port 40H dedicated to this function. The 8 bits output from port 40H enable or disable the corresponding bank(s) in memory. A set bit "1" in the corresponding bit position will enable the memory bank. A reset bit "0" will disable it.

## 2.3 Direct Memory Access Override

The 16KZ RAM card also features Cromemco Direct Memory Access Override, a powerful hardware feature which allows memory blocks residing in different memory banks , with identical or overlapping addresses, to be accessible to DMA transfer.

Switches 3 and 4 in the 4-place DIP switch at the middle top of the card control this function.

Switch 4, when in the UP position, enables the DMA override for the entire block. When DOWN, the DMA override is disabled. Switch 3, when in the UP position, locks out the block of memory during DMA transfer. When in the DOWN position, the memory is accessible to DMA regardless of whether or not it resides in the currently active memory bank. The setting of Switch 3 is only relevant if Switch 4 is UP and then only during DMA operations. Normally both Switch 3 and Switch 4 are left in the DOWN position.

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### 3.0 ASSEMBLY INFORMATION

### 3.1 Assembly Instructions

The Cromemco 16KZ RAM card incorporates state-ofthe-art circuit design. Mechanically, it will tolerate some jarring or an occasional fall, the card must be inspected, however, to check for unstuck 'cold' solder joints, fractured leads, bent contact pins, and/or damaged ICs.

Electrically, the 16KZ RAM is more sensitive. Because of the extremely high operating speed of this memory, some parts have narrow critical tolerances. An inappropriate voltage can destroy them. Please do not attempt to operate this card without first running the supplied diagnostic tests after assembly, or after unpacking. The MOS memory ICs can be easily damaged by static electricity, so care must be taken in handling these components.

In constructing the card, remember to use a lowwattage soldering iron with solid or rosin-core solder. Never use acid-core solder on any electronic equipment. Heat both the wire or pin and the PC terminal; apply solder to the junction of tip and board until the solder 'flows'; remove heat and let stand until cool. Snip leads where appropriate. Pay particular attention to insure a good solder joint at the pins of the IC sockets. A 'cold joint' here may result in a board that destroys each chip that is installed into it, causing much confusion and troubleshooting headaches. Push hard when inserting ICs into their sockets to make sure they are seated properly. Take particular care to see that every pin of every IC is properly engaged in its socket. Refer to Assembly Information Section 3.4 diagram.

## 3.2 Initial Checkout

In building the 16KZ RAM card, proceed in installing the sockets and discrete components according to the assembly diagram included on page 7. Before inserting the integrated circuits into their sockets, you should check the power supply voltages. Verify that the regulators are performing properly, outputting -5V, +5V, and +12V.

## 3.3 Cautions

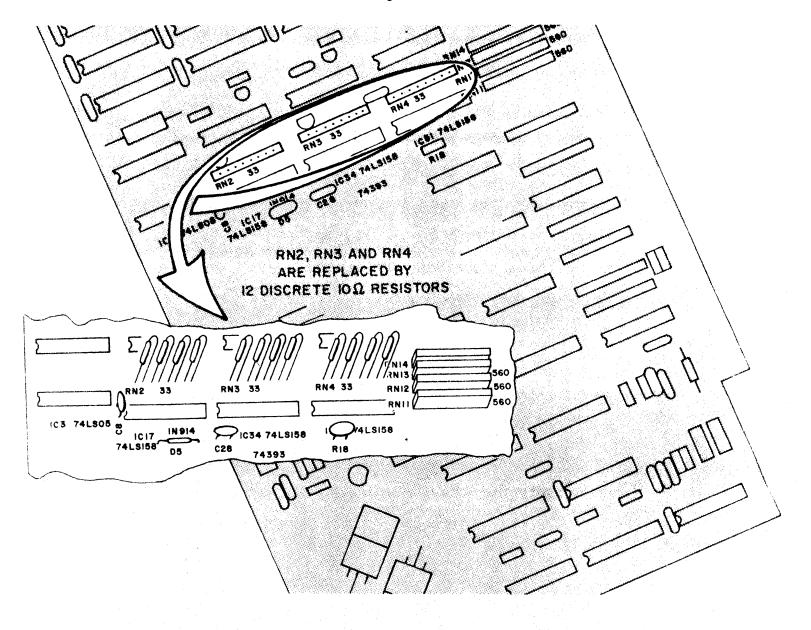
Never install or remove additional parts or circuit cards from an electronic device with power on.

Do not operate the 16KZ in a microcomputer system without a CPU card furnishing a two-phase clock line.

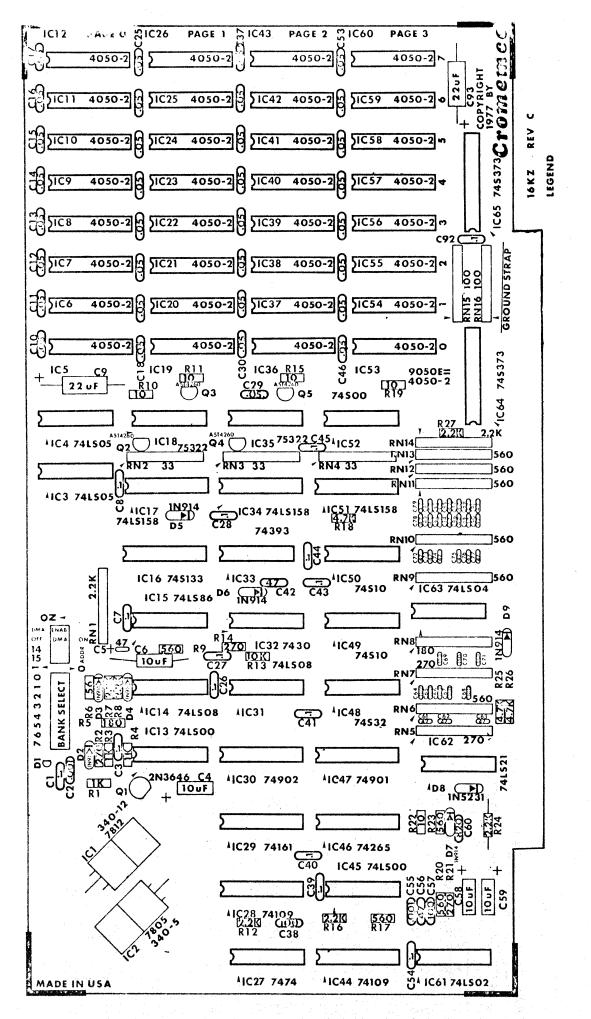
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#### 3.4 Parts Placement Diagram

The Parts Placement Diagram on the following page shows the positioning of parts on the 16KZ pc board. Note that R10, R11, R15, and R19 are now 22 ohm resistors rather than 10 ohm resistors as shown. C42 should be a 220 pF capacitor rather than 47 pF as shown. Twelve discrete 10 ohm resistors may be substituted for the 33 ohm resistor networks RN2, RN3, and RN4. If this substitution is made the 10 ohm resistors should be installed as shown in the diagram below:



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7

PARTS PLACEMENT DIAGRAM 16KZ -1

3

#### 4.0 THEORY OF OPERATION

### 4.1 Bank Select Logic

The bank select logic circuit decodes commands sent to output port 40H by the CPU to determine if the memory bank in question should be active. If the CPU sends a logic one to any bit position for which the bank select switch is ON, the board will be enabled. Otherwise, the board will disable. IC16 decodes the combination for SOUT, PWR, and address 40H and sends a clock pulse to the bank select circuitry. The combination of open collector inverters IC3 and 4 does an AND-OR operation to detect the correct bank IC28 stores the current bank status, sends state. it to the LED D2 for indication, and controls the board enable gate IC32. The AND gates IC31 in combination with some discrete components cause the bank  $\emptyset$  switch setting to control the board status whenever PRESET and  $\overline{POC}$  are pulsed. Thus the bank  $\emptyset$  switch determines the state the board comes up in whenever a RESET occurs.

## 4.2 Direct Memory Access Override

IC13 in conjunction with the DMA ENABLE and DMA OFF switches allows DMA operations to override the current bank selection if desired. If the DMA ENABLE switch is open (i.e. away from the top card edge),

- 8 -

then the current bank select FF state governs the board state during DMA operations. In this case, the DMA OFF switch has no effect. If the DMA ENABLE switch is closed, (i.e. towards the top card edge), then the DMA OFF switch determines whether the board is enabled during DMA operations. If the DMA OFF switch is open (away from the top card edge), then the memory card is enabled for DMA operations when addressed. If the DMA OFF switch is closed (towards the top card edge), the memory card is unconditionally disabled during all DMA operations.

Proper use of the DMA ENABLE and DMA OFF switches will permit DMA devices, such as video graphic display generators, to remain "in contact" with their own dedicated memory area regardless of the current memory bank selection. This prevents loss of the image when banks are switched. Of course, all memory cards in an address range where bank switching is used in conjunction with DMA ENABLE must have the DMA ENABLE switching capability to prevent bus conflicts.

#### 4.3 Board Enable Decode

The overall board status is decoded by IC32. Address selection uses exclusive-OR logic gates in conjunction with two dip switch sections to select the 16K address block for which the board is active. If any of the status lines SINP, SOUT, or SINTA goes high, the board is disabled. Also, any device pulling the MDSBL bus

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line (pin 67) low will disable the memory board. This permits a ROM bootstrap to overlap the memory area if desired. If the bank select and other conditions are met, then the output of IC32 goes low to enable the 16KZ to perform memory cycles.

#### 4.4 Chip Enable Generation

The 16KZ uses a direct read process for generation of the RAM chip enable signals. In general, whenever the address and other conditions are correct for addressing a particular RAM, the chip enable (CE) input will go high (+12V) if a memory cycle request occurs. This is when either MWRITE, PDBIN, or SM1 go high, or MREQ Since the bus signals are used directly to goes low. control the CE generation, all devices sending memory cycle signals on the bus must use a format similar to the 8080 and send only signals for complete memory Short pulses or address changes while CE is cycles. high will usually cause the RAM area addressed to fail to restore the data after reading it out. The data then changes state and is lost. Direct read operation was chosen to permit the shortest possible memory access operation and thereby allow operation at 4 MHz with the Cromemco ZPU without wait states.

Decoding of the bus signal combinations giving valid CE operation occurs in IC47. Address line AØ determines whether the CE pulse will occur on pin 12 ( $\Lambda Ø=0$ ) or pin 11

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 $(A\emptyset=1)$ . During CPU operations, CE pulse outputs can occur only if the address enable input is low and the gating pulse input H is high. During DMA operation the gating input H is held low. In general, gating input H is used to turn off the CE pulse whenever conditions requiring it occur. IC62 combines a number of these inhibiting conditions to produce the CE gating pulse. The signals of primary importance during CPU operation are the RFSH bus signal on pin 66, and the gating FF output from IC28 pin 7. The gating FF, IC28, takes pin 7 high whenever a CE pulse is allowed. Ιf the current CE pulse lasts more than 8 cycles of  $\emptyset 2$ , then the QD output of IC29 goes high. This sets IC28 and its pin 7 goes low to terminate the CE pulse. This prevents the CE pulse length from exceeding the RAM specifications if the CPU enters a wait state during a memory cycle. The wait state situation occurs primarily during front panel single step and reset operations, but could come from a hardware item elsewhere. Also, if a refresh cycle begins, CCDSBL goes low, or PHLDA goes high, IC 28 goes low to prevent CE pulses from IC47. When normal CPU operation resumes, a logic low level output from IC30 pin 10 causes IC28 to take pin 7 high again.

#### 4.5 Chip Enable Control Logic

The chip enable pulses from IC47 go first through IC48, which stretches the trailing edges to eliminate any low going glitches which may be generated in IC47. The CE signals then go to IC49 and IC50 for selection of the block of 4K bytes to be accessed. The NOR gate IC61 turns off the CE pulse when the board is unaddressed or during a refresh cycle. IC52 inserts the refresh pulse, and IC18 and IC35 amplify the TTL signal to logic levels of 0 and +12V for the RAMs. The 75332's employ an external PNP transistor to pull their outputs up to +12V.

The CE generation and control logic divides the RAM array into 4K blocks depending on the states of AØ and A8. This permits fast DMA devices such as the TV Dazzler to use ripple addressing with either AØ or A8 as the most rapidly changing address. Minimum access times result, with the read process occurring in a manner similar to static RAMs. In order to use this mode, all addresses and control lines must change at the same time.

#### 4.6 RAM Array

The RAM array consists of 4 blocks or rows of 4K x 1 RAM chips, with like bit positions bussed together. All the similar address and control lines are tied together, with the CE pulse determining which row responds.

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Address data comes from multiplexers IC19, IC36, and IC53. These determine whether the RAM's use the CPU bus or the refresh counter for addressing. During write operations, IC64 transmits data from the CPU DO bus to the RAM chip data pins. The 3 state output of IC64 turns ON whenever an MWRITE pulse occurs. A stretching network with IC46 prolongs the MWRITE pulse trailing edge to allow for propagation delays through the CE logic. Data entry into IC64 is enabled whenever either PWR or PRDY are low. This allows the memory write cycle to complete after the CPU changes DO for the next advanced status.

Data read out of the RAM array is latched into IC65. Thus it is available to the CPU and front panel after the memory completes its cycle. PDBIN, SMEMR, and board enable control gating of the data onto the DI bus. The latch enable signal comes from IC47 and goes high whenever the RAM array is read or written for data.

### 4.7 Refresh Cycle Generator

This memory board uses an M1 refresh state process. Advantage is taken of the fact that 8080 and Z80 CPU's use at least 4 clock cycles for their M1 states to fetch and decode instructions. The normal data fetch occurs during the first 2 clock cycles, and then memory

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refresh occurs during the 3rd and 4th clock cycles of Ml. When a coincidence of SM1.PSYNC=1 occurs at a  $\emptyset$ 2 positive going edge, IC29 pin 5 goes high to note this. One  $\emptyset$ 2 cycle later, IC29 pin 9 goes high to begin a refresh sequence. During refresh, IC61 turns off any CE signals from IC47. At the first  $\emptyset$ 2 negative going edge after refresh begins, IC44 pin 9 goes low to turn ON the CE's for all RAM's and refresh their data. One  $\emptyset 2$  cycle later, IC44 turns OFF, completing the refresh and incrementing the refresh address counter IC33. IC29 then turns OFF and returns the RAM to CPU control. If the RAM is used with a Z80, IC14 uses the  $\overrightarrow{RFSH}$  signal to prevent action by the CPU refresh pulse on  $\overline{MREQ}$ . Otherwise, some wait state conditions may cause the generation of CE glitches. When the refresh cycle begins, IC 45 causes IC28 pin 7 to go low. It stays this way until the trailing edge of SMI clocks IC 44 pin 4, which causes IC30 to make IC28 pin 7 high again. IC44 clocks at the trailing edge of SMI and PHLDA and the leading edges of MWRITE. During times when CPU operation is suspended, IC30 pin 9 goes high, causing IC29 to count. After 8 cycles of  $\emptyset 2$ , the CE outputs of IC47 are disabled. After 16 cycles of  $\emptyset 2$ , IC29 pin 15 goes high, causing autonomous memory refresh cycles. These refresh cycles continue to occur once per 16 Ø2 cycles until CPU operation resumes. Two sections of IC49 arbitrate between MWRITE and refresh pulses to prevent CE conflicts during front panel write operations with the CPU stopped.

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#### 4.8 Reset Circuitry

The reset circuitry takes care of the special CE management problems that occur with dynamic memories using a direct read process. When the  $\overrightarrow{PRESET}$  line goes low, IC13 and Q5 immediately pull down the PRDY line. This causes the CPU to halt during execution of the current memory cycle. The memory board then times out eight  $\emptyset$ 2 cycles and IC28 pin 7 turns off the CE pulse. The CPU board <u>must have</u> a 10 µsec delay network in series with its  $\overrightarrow{PRESET}$  input as described in Section 7.0.

Provision of a 10 µsec delay permits the memory board to turn off before the CPU terminates the current operation. This is very important, as it has been discovered that some CPU chips immediately abort the current cycle in process whenever the <u>PRESET</u> line goes low. As a result, short CE pulses could result and cause loss of data. Multiple bouncing by the reset switch when activated aggravates the problem.

When the PRESET line is released, IC14 produces a delay of about 50 msec to allow for multiple switch bouncing. At the end of this time, IC13 and IC31 cause the data at memory location  $\emptyset$  to be read into the data latch IC65. After another 50 µsec, IC13 and Q5 release the PRDY line, allowing CPU operation to resume if in the run state. This procedure prevents the occurence of partial memory cycles and resulting data loss caused by the reset switch bouncing.

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#### 5.0 16KZ MEMORY TEST

The 16KZ Memory Test loads and executes at any address except 101 H through FFFH. It requires at least 4K of RAM addressed at 0 and situated in all eight banks. (Set the address DIP switches of the Cromemco 4KZ or 16KZ to 0 and raise all eight of the bank-select DIP switches.)

In particular, it can be stored and executed in a pair of 2708 PROMs at any address in upper memory. The program is compatible with either the Z80 or the 8080 instruction set.

The Memory Test can check 16KZ cards at any address except  $\emptyset$  and in any bank. It includes five different tests.

 The Peak test shifts a one in a field of zeroes through the card. It loads a byte with one bit high into the top location of the card. The next location gets the byte shifted left,say. After the 1 is shifted into the carry flag, the shift direction is reversed. Each byte is checked after it is written and again after the entire card is loaded. The test is repeated for each of the 18 possible ways of loading such a pattern.
 The Valley test is like the Peak test except

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that it uses a zero in a field of ones.

- 3. The Delay test checks long-term memory retention. The card is filled with a pattern and then tested to see if it can retain the pattern for at least 6 seconds (at 4 MHz). The test is repeated for each of several patterns.
- The MI test checks the capability of the card to be read during MI machine cycles.
- 5. The Bank test determines in which banks the card appears.

## 5.1 Using the Test

The Memory Test checks 16KZ cards addressed at 4, 8 or C (i.e. 4000H, 8000 or C000H).

Assume that the Memory Test resides at 1000H and that we wish to check cards at 8 and C in bank  $\emptyset$  and at 4, 8 and C in bank 7.

Make sure that there is RAM at ∅ in all banks. Execute 1000H. When prompted by 'BANK: ' type the bank number followed by a space. After the prompt 'CARDS: ' type the card numbers separated by spaces. The last card number should be followed by a carriagereturn. The prompt 'BANK: ' will again be issued. If no further cards are to be tested type a carriage return.

BANK: Ø CARDS: 8 C (CR) BANK: 7 CARDS: 4 8 C (CR) BANK: (CR)

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If an entry error is made, a '?' will be printed, the card queue cleared and prompts mode to begin again.

Testing of the cards continues until either the ESCAPE key or CONTROL-'Q' is depressed. (See Control Functions below.)

#### 5.2 Error Print-Out

If any errors occur in the Peak, Valley or Delay test, an image of the card will be printed indicating the physical locations of the RAMs in which the errors occurred. In the following example errors occurred in bits 1 and 3 of rows 1 and 2, respectively, of card C in bank 7.

-Ø- -1- -2- -3- -4- -5- -6-(CARD C) - 7 -(BANK 7) Ø: . . . . . . . . . 1: . . . PVD . . . . . . . . . 2: . . . PVD 3: . . . . . . . . . . . .

The MI test and the Bank test are only made if there are no errors in the first three tests.

#### 5.3 Control Functions

 Pushing CONTROL - 'P' causes a print-out of the image of the card currently under test. After print-out the test resumes at the point it was interrupted.

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- CONTROL 'E' causes a listing of all the cards in which errors have occurred. The test then resumes at the point it was interrupted.
- 3. ESCAPE or ALT MODE causes a print-out of the current card image followed by termination of the test and prompting for a new test.
- CONTROL 'S' causes the remainder of a printout to be skipped. The test then resumes as if the print-out had been finished.
- 5. CONTROL 'Q' causes the Memory Test to be quit. Transfer to the warm-start entry point (E008) of the Z80 Monitor is made.

## 5.4 Loading the Paper Tape

The memory test program assumes that data transfer occurs on I/O port 1. Status flags are on input port  $\emptyset$ . The data-available flag is on bit 6 of input port  $\emptyset$ . The transmitter-buffer-empty flag is on bit 7 of input port  $\emptyset$ . Both flags are active high.

The following program can be used to load the binary paper tape of the memory into RAM at location  $\emptyset$ .

1ØØØ 1ØØ3	21 ØØ DB ØØ	ØØ	LD HL, Ø LOOP: IN A, Ø
	E6 4Ø		AND 4ØH
	CA Ø3	1Ø	JP Z, LOOP
	DB Ø1		IN A, 1
	77		LD(HL), A
	23		INC HL
	C3 Ø3	$1 \emptyset$	JP LOOP

The tape can also be loaded with the Cromemco Monitor by typing R  $\emptyset$  6 $\emptyset$  $\emptyset$  (CR)

#### 6.0 TROUBLESHOOTING

#### 6.1 Common Problems

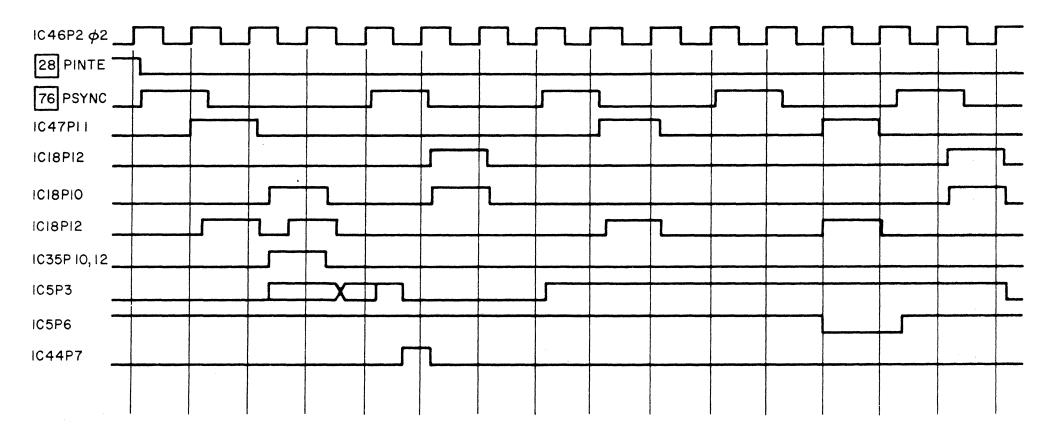
- 1. If the card has been tested and examined and found to be unreliable in reading and writing data, check that pin 11 on IC64 turns on and off with  $\overline{PWR}$  (from S-100 bus pin 77) and that pin 1 on IC64 stays at a low logic level for 100 to 150ns after the trailing edge of MWRITE (from S-100 bus pin 68).
- 2. The card has been extensively tested. It functions properly in a simple program, such as JMP to Ø, but will not run a longer program of normal complexity. A number of possible defects must be explored:
  - a. Two address lines in memory may have shorted together.
  - b. SMI (on S-100 bus pin 44) at IC47 pin 2 may rise
    before memory addresses have stabilized.
  - c. One of the RAM 4050 chips has a bad memory bit or an internal addressing fault.
  - d. The address line may have shorted to ground or +5.
  - e. The +12V line may not be regulated properly. Recheck.

Remember, to troubleshoot the 16KZ RAM card effectively, an oscilloscope with a bandwidth greater than 15 MHz must be used. Slower oscilloscopes cannot represent the waveshapes accurately.

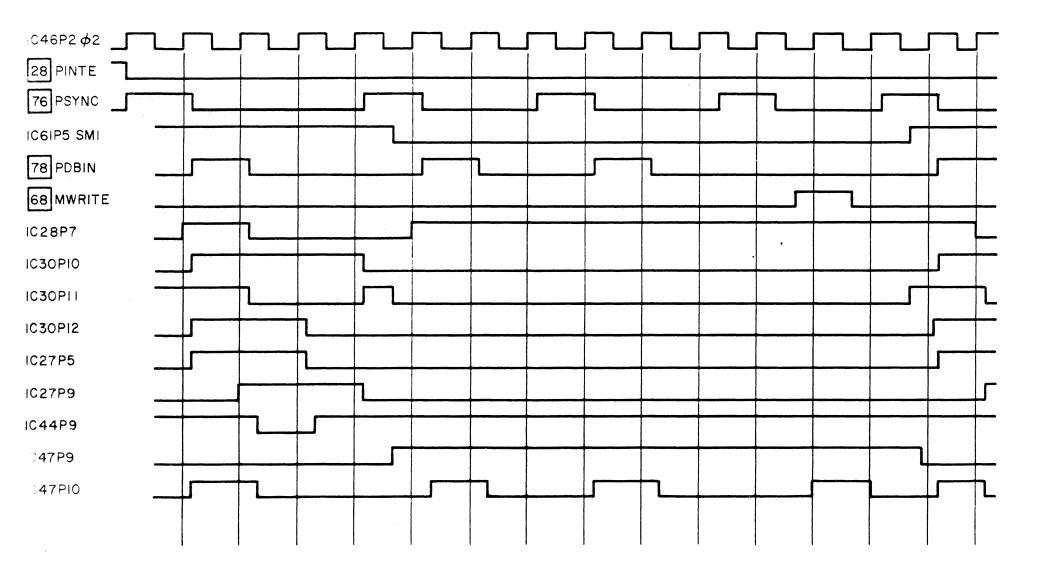
-20-

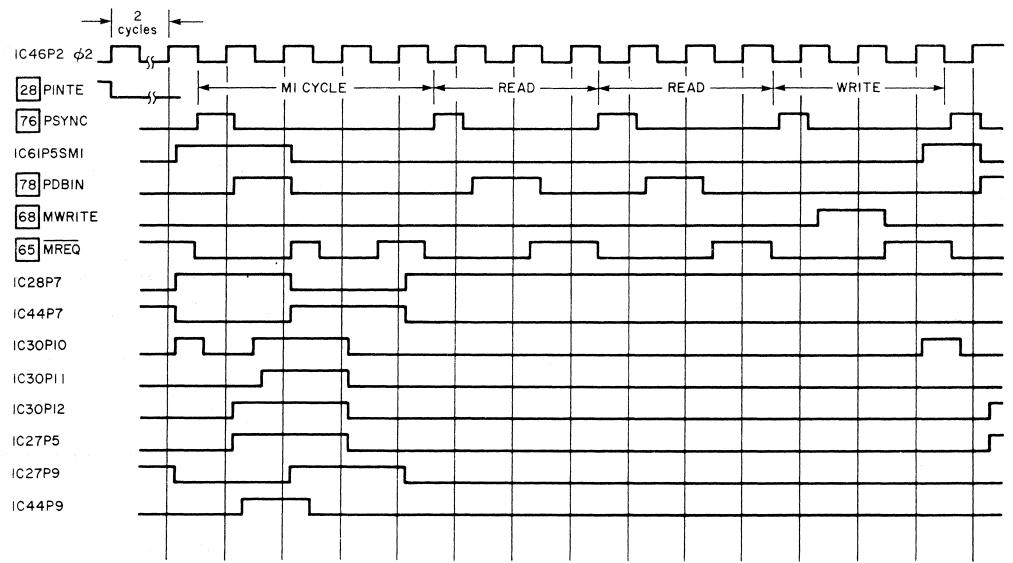
6.2 Timing Diagrams

# OPERATION WAVEFORMS FOR 8080 CPU



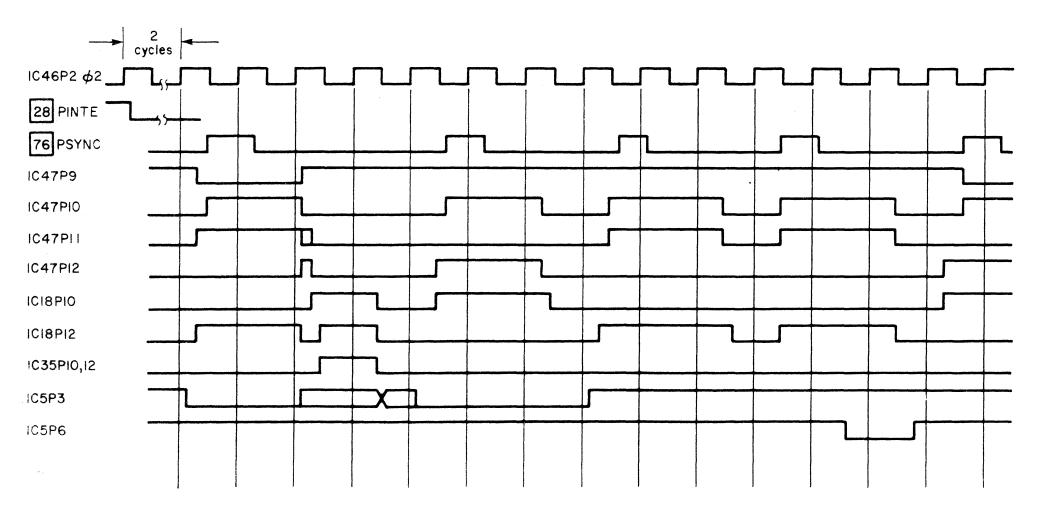
OPERATION WAVEFORMS FOR 8080 CPU





OPERATION WAVEFORMS FOR CROMEMCO ZPU

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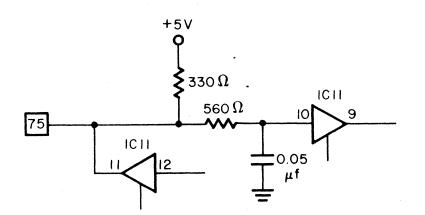
OPERATION WAVEFORMS FOR CROMEMCO ZPU

#### 7.0 SYSTEM COMPATIBILITY INFORMATION

The Cromemco 16KZ RAM card offers expandability and high-speed performance and was designed to be compatible with all Cromemco products and virtually all other well-designed S-100 bus based systems. To assist users who wish to upgrade existing hardware by taking advantage of these features, interface procedures for selected systems are described below:

## Cromemco ZPU Rev A or B

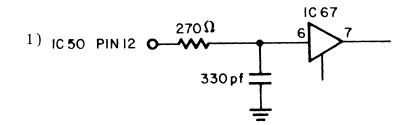
Modifications are not required for more recent revisions of the Cromemco ZPU card. For Rev A or B, modify the RESET circuit as below to assure memory integrity following a reset signal:



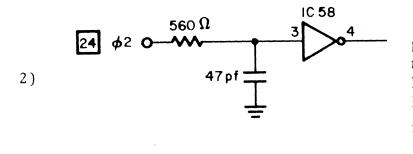
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#### Cromemco Dazzler

The Cromemco Dazzler is designed for operation with static RAM memory. The Dazzler can however be modified to operate with the 16KZ dynamic card as shown below:



Prevents display breakup on 64 x 64 color mode.



Needed in early model Altairs to prevent spikes on Ø2 from mislocking Dazzler DMA state machine. (Prevents random changes in display memory area)

3) There are 3 pads on board 2 just above IC57 in a triangle. Cut the trace on the component side which runs between the two leftmost pads. This trace connects IC57P12 to IC49P1. Put a wire jumper so that IC49P1 connects to IC57P11 instead. This eliminates the bus float state at DMA transfer.

4) RFSH output on 67 must be disabled on Dazzler Rev B and below. Remove IC66 and bend out pin 12 so it does not go into socket contact. Replace in socket.

# Digital Systems Disc Controller Interface

On the S-100 bus connector edge of the controller interface card, cut the trace connecting bus line [67]

# 16KZ REV C PARTS LIST

# Capacitors

C 1	.1 Disc
2	.001 Disc
3	.1 Disc
4	10 UF Tant
5	47 Pf Mono
6	10 UF Tant
7	.1 Disc
8	.1 Disc
9	22 UF Tant
10-25	.05 Disc
26-28	.1 Disc
29-37	.05 Disc
38	100 Pf Disc
39-41	.1 Disc
42	220 Pf Disc
43-45	.1 Disc
46-53	.05 Disc
54	.1 Disc
55	.001 Disc
56	47 Pf Disc
57	100 Pf Disc
58-59	10 UF Tant
60	820 Pf Disc
61-63	47 Pf Mono
64-68	100 Pf Mono
69-71	150 Pf Mono
72-91	47 Pf Mono
92	.1 Disc
93	22 UF Tant

	Socke	ts
18	Pin	32
20	Pin	2
16	Pin	10
14	Pin	19

# Misc

- 1 8 Pole Dip Switch
- 1 4 Pole Dip Switch
- 1 Heatsink
- 4 6-32 Pan Head Screws
- 4 6-32 Hex Nuts
- 4 6-32 Hex Nuts
- 1 PC Board
- 1 Paper tape listing of memory test program
- 1 16KZ instruction manual schematic diagram

# Diodes

D1	LED,	T1L-211
D2 - D7		IN914/IN4148
D8		IN5231
D9		IN914/IN4148

# Transistors

2N3646 1 A5T4260 4

# Resistor Networks

RN1	2.2K	,	Sip,	7	Resistors,	8	Pin
RN2,3,4	33	,	Sip,	4	Resistors,	8	Pin
RN 5	270	,	Sip,	4	Resistors,	8	Pin
RN6	560	,	Sip,	4	Resistors,	8	Pin
RN7	270	,	Sip,	4	Resistors,	8	Pin
RN8	180	,	Sip,	4	Resistors,	8	Pin
RN9-13	560	,	Sip,	4	Resistors,	8	Pin
RN14	2.2K	,	Sip,	7	Resistors,	8	Pin
RN15-16	100	,	Sip,	4	Resistors,	8	Pin
Resistors							

R1	1 K	R10	22	R19	22
2	270	11	22	20	560
3	1 K	12	2.2K	21	270
4	1K	13	10K	22	10
5	180	14	270	23	560
6	56	15	22	24	2.2K
7	2.2K	16	2.2K	25	4.7K
8	2.2K	17	560	26	4.7K
9	560	18	4.7K	27	2.2K

# 16KZ REV C PARTS LIST

IC	1	7812/340-12
	2	7805/340-5
	3	74LS05
	4	74LS05
	5-12	TMS4050-2/9050E
	13	74LS100
	14	74LS08
	15	74LS86
	16	74S133
	17	74LS158
	18	75322
	19-26	TMS4050-2/9050E
	27	7474
	28	74109
	29	74161
	30	74902 ROM2
	31	74LS08
	32	7430
	33	74393
	34	74LS158
	35	75322
	36-43	TMS4050-2/9050E
	44	74109
	45	74LS00
	46	74265
	47	74901 ROM1
	48	74S32
	49-50	74S10

IC5174LS1585274S0053-60TMS4050-2/9050E6174LS026274LS216374LS0464-6574S373

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#### 9.0 WARRANTY

Your factory-built 16KZ 4 MHz RAM card is warranted against defects in materials and workmanship for a period of 90 days from the day of delivery. We will repair or replace products that prove to be defective during the warranty period provided that they are returned to Cromemco. No other warranty is expressed or implied. We are not liable for consequential damages.

Should your factory-built 16KZ 4 MHz RAM card fail after the warranty period it will be repaired, provided that it is returned to Cromemco, for a fixed service fee. We reserve the right to refuse to repair any product that in our opinion has been subject to abnormal electrical or mechanical abuse. The service fee is currently \$70 and is subject to change.

Your assembled 16KZ 4 MHz RAM card kit will be repaired, provided that it is returned to Cromemco, for a fixed service fee. We reserve the right to refuse to repair any kit that in our opinion has not been assembled in a workmanlike manner or has been subject to abnormal electrical or mechanical abuse. Payment of the service fee must accompany the returned merchandise. The service fee is currently \$70 and is subject to change.

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#### 16KZ ENGINEERING NOTICE

C42 should be a 220 pf capacitor rather than 47 pf as shown.

R10, R11, R15, R19 should be 22 ohms, not 10 ohms.

RN6 and RN9-RN13 may optionally be supplied as 470 ohm networks instead of the 560 ohm networks as shown.

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C42 should be a 220pF capacitor rather than 47pf as shown.

R10, R11, R15, R19 should be  $22\Omega$ , not  $10\Omega$ .

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Twelve discrete  $10\Omega$  resistors may be substituted for the  $33\Omega$  resistor networks RN2, RN3, and RN4. If this substitution is made, the  $10\Omega$ resistors should be installed as shown in the diagram. Similarly, discrete resistors may be substituted for  $270\Omega$  networks RN5 and RN7, and for  $560\Omega$  networks RN6 and RN9-13. These resistors should be installed in a similar manner in their respective locations.

